

N-channel LFPAK 60 V 6.4 mΩ standard level MOSFET

Rev. 02 — 30 March 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

1.4 Quick reference data

Table 1. Quick reference

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

Table 1.	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	89	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Avalance	he ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	143	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 60 \text{ A};$	-	9.6	-	nC
Q _{G(tot)}	total gate charge	$V_{DS} = 30 V$; see <u>Figure 14</u> and <u>15</u>	-	45	-	nC

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Table 1.	Quick reference continued					
Symbol	Parameter Conditions		Min	Тур	Max	Unit
Static cl	naracteristics					
R_{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 100 \text{ °C}; \text{ see } \overline{Figure \ 12} \end{array}$	-	-	10.2	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	4.95	6.4	mΩ

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate	Qj	
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline \\ \hline \\ 1 \\ 2 \\ 3 \\ 4 \\ \end{array}$	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

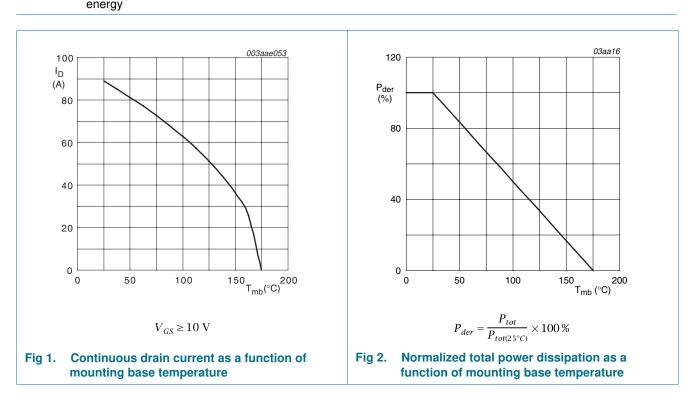
Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PSMN7R0-60YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669		

4. Limiting values

Table 4. Limiting values

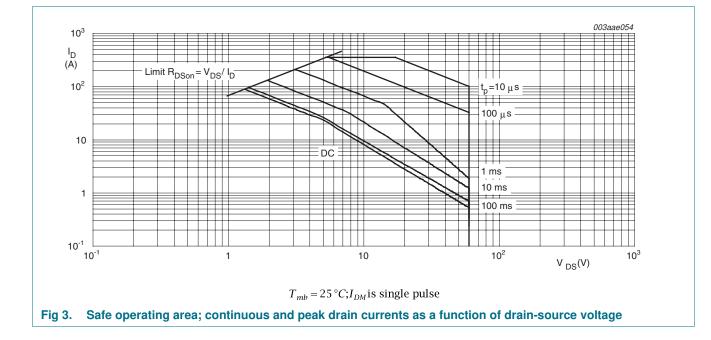
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	$T_i \ge 25 \text{ °C}; T_i \le 175 \text{ °C}$	-	60	V
	drain-gate voltage	$T_i \ge 25 \text{ °C}; T_i \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		60	v
V _{DGR}		$1j = 20$ G, $1j = 175$ G, $11_{GS} = 20$ M2	-20	20	V
V _{GS}	gate-source voltage	100 °C	-20		
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	63	A
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	-	89	А
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	356	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	117	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dr	ain diode				
I _S	source current	T _{mb} = 25 °C	-	89	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	356	Α
Avalanche	e ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_{D} = 89.1 A; V_{sup} ≤ 60 V; R_{GS} = 50 $\Omega;$ unclamped	-	143	mJ



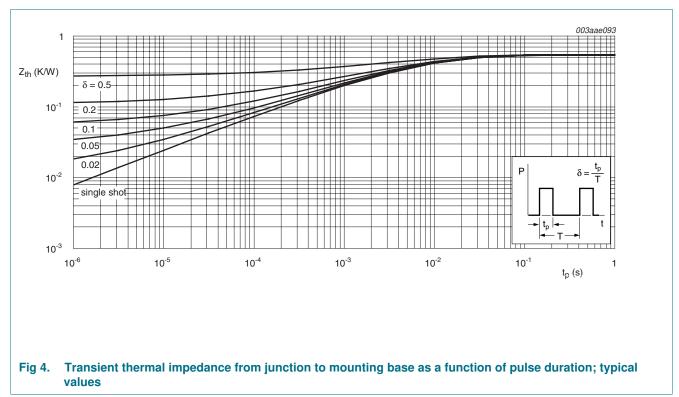
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.54	1.28	K/W



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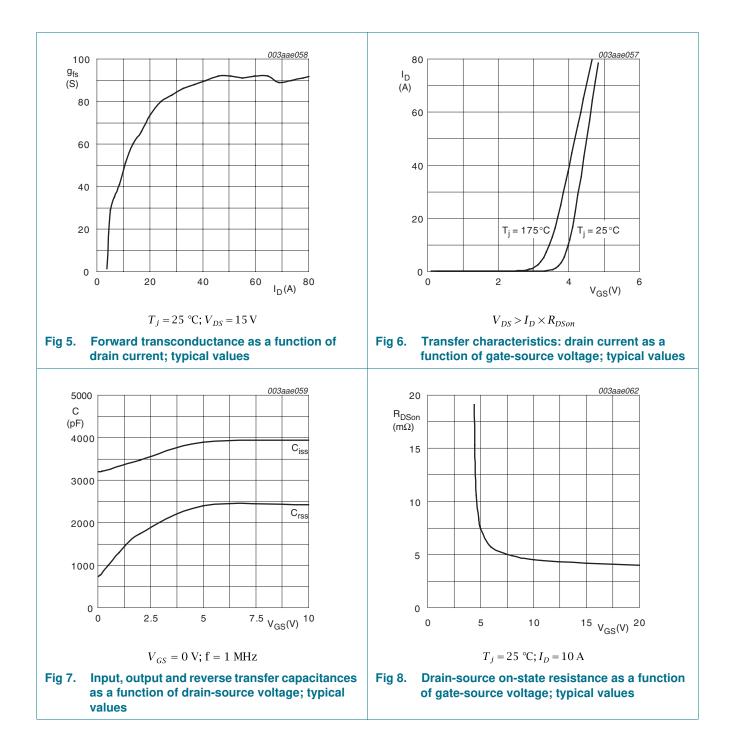
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 10</u> and <u>11</u>	2	3	4	V
V _{GSth}		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{see } \frac{\text{Figure } 11}{1}$	-	-	4.7	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; \text{see } Figure 11$	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.04	2	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	9.3	14.7	mΩ
	resistance	V_{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	10.2	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	4.95	6.4	mΩ
R _G	gate resistance	f = 1 MHz	-	0.65	1.5	Ω
Dynamic	characteristics					
$Q_{G(tot)}$ total gate charge	total gate charge	I_D = 60 A; V_{DS} = 30 V; V_{GS} = 10 V; see Figure 14 and $\underline{15}$	-	45	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	37.6	-	nC
Q _{GS}	gate-source charge	I_D = 60 A; V_{DS} = 30 V; V_{GS} = 10 V; see Figure 14	-	14.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge			7.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	6.8	-	nC
Q _{GD}	gate-drain charge	I_D = 60 A; V_{DS} = 30 V; V_{GS} = 10 V; see Figure 14 and $\underline{15}$	-	9.6	-	nC
V _{GS(pl)}	gate-source plateau voltage	$V_{DS} = 30$ V; see Figure 14 and 15	-	4.9	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C};$	-	2712	-	pF
C _{oss}	output capacitance	see Figure 16	-	366	-	pF
C _{rss}	reverse transfer capacitance		-	202	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 0.5 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	19.9	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	20.3	-	ns
t _{d(off)}	turn-off delay time			37.9	-	ns
t _f	fall time		-	12.6	-	ns
	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 17}{100000000000000000000000000000000000$	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S} = 20 \text{ A}; \text{ dI}_{\rm S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{\rm GS} = 0 \text{ V};$	-	41.9	-	ns
		$V_{DS} = 30 V$				

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Product data sheet

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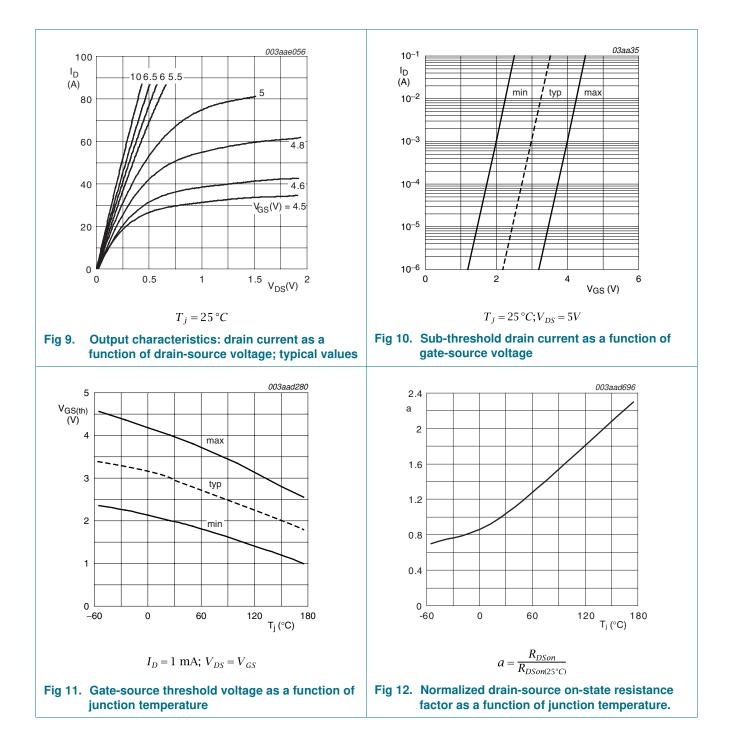
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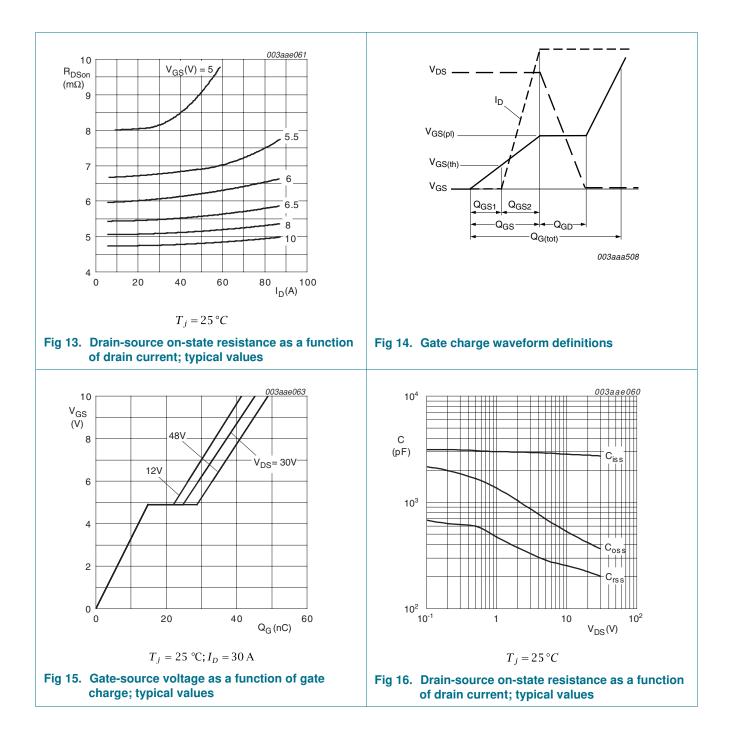
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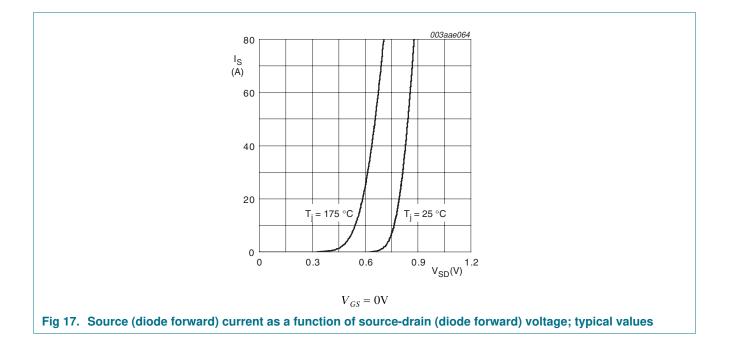
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7. Package outline

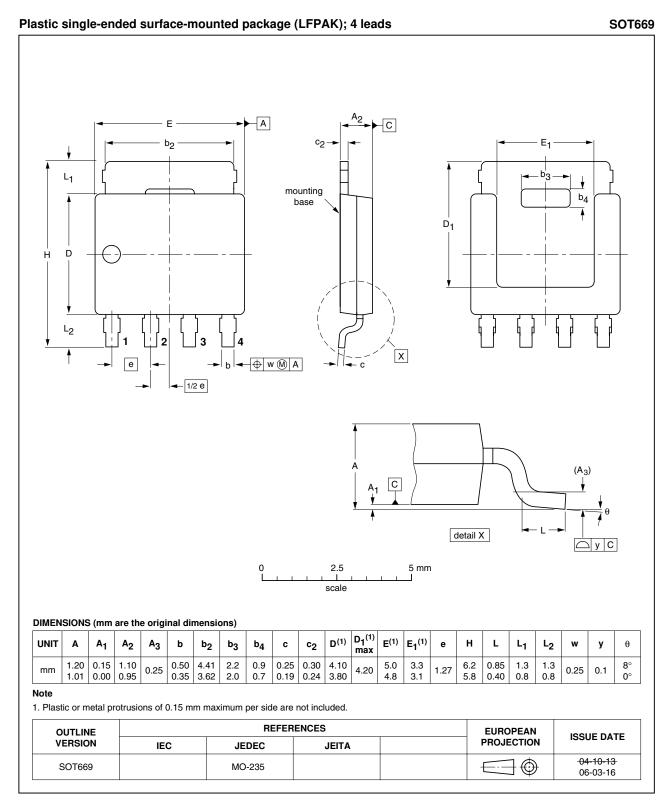


Fig 18. Package outline SOT669 (LFPAK)

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-60YS_2	20100330	Product data sheet	-	PSMN7R0-60YS_1
Modifications:		nged from objective to pr anges to content.	oduct.	
PSMN7R0-60YS_1	20100112	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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